

RF Matrix Amplifier

Description

The CXA2570N is an IC developed for the RF signal processing of compact disc players.

Features

- Wide band RF signal processing
- RF system VCA circuit
- RF system equalizer (supports CAV mode)
- Supports pickups with built-in RF summing amplifier
- Low power consumption mode (EQ Pass mode)
- RW/ROM switching mode

Functions

- RFAC summing amplifier, equalizer, VCA
- RFDC summing amplifier
- Focus error amplifier
- Tracking error amplifier
- Automatic power control
- VC buffer amplifier

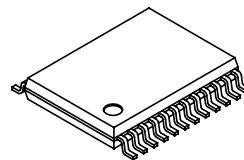
Applications

CD-ROM/RW compatible systems

Structure

Bipolar silicon monolithic IC

24 pin SSOP (Plastic)



Absolute Maximum ratings

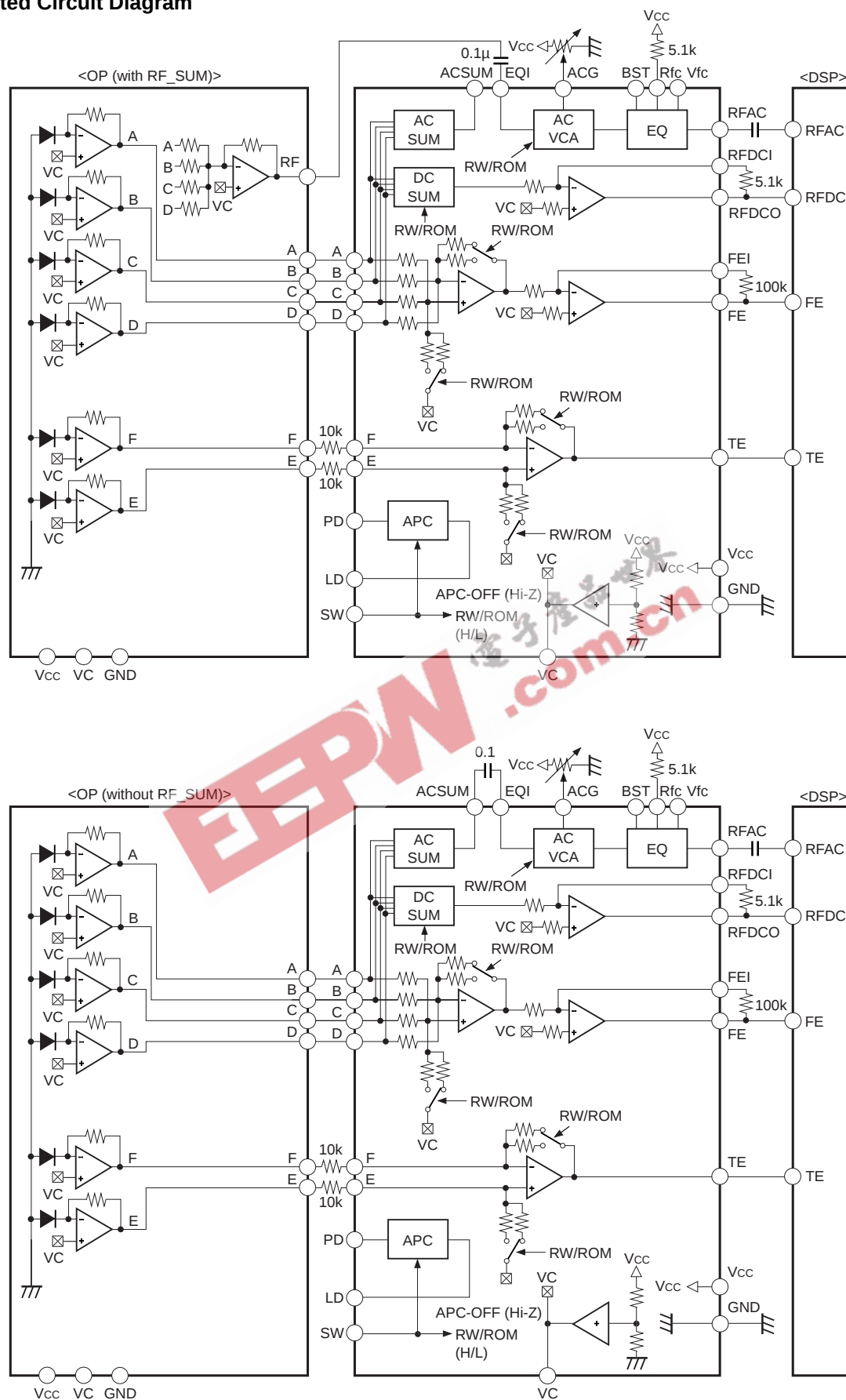
• Supply voltage	Vcc	7	V
• Operating temperature	Topr	−20 to +75	°C
• Storage temperature	Tstg	−65 to +150	°C
• Allowable power dissipation	Pd	620	mW

Operating Conditions

• Supply voltage	Vcc – GND	3.0 to 5.5	V
• Operating temperature	Topr	−20 to +75	°C

Sony reserves the right to change products and specifications without prior notice. This information does not convey any license by any implication or otherwise under any patents or other right. Application circuits shown, if any, are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits.

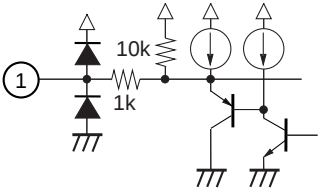
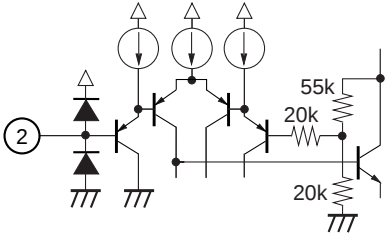
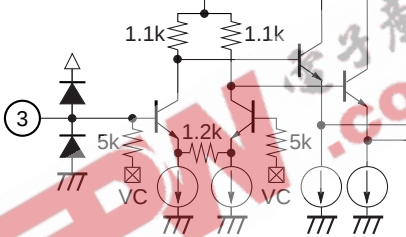
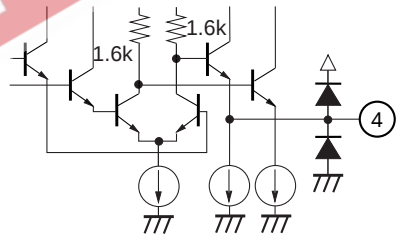
Connected Circuit Diagram



Pin Description

Pin No.	Symbol	I/O	Description
1	LD	Out	APC amplifier output.
2	PD	In	APC amplifier input.
3	EQ_IN	In	RFAC system VCA block and EQ block input.
4	AC_SUM	Out	RFAC system RF SUM output.
5	GND	In	Ground.
6	A	In	A signal input.
7	B	In	B signal input.
8	C	In	C signal input.
9	D	In	D signal input.
10	E	In	E signal input.
11	F	In	F signal input.
12	SW	In	Mode switching signal input.
13	RFAC	Out	RFAC signal output.
14	FE	Out	Focus error signal output.
15	FEI	—	FE amplifier virtual ground.
16	TE	Out	Tracking error signal output.
17	Vcc	In	Vcc.
18	RFG	In	RFAC system VCA block low-frequency gain adjustment.
19	BST	In	EQ boost amount adjustment range.
20	VFC	In	EQ cut-off frequency adjustment.
21	RFC	In	EQ cut-off frequency adjustment.
22	VC	Out	VC voltage output.
23	RFDCO	Out	RFDC signal output.
24	RFDCI	—	RFDC amplifier virtual ground.

Pin Description and Equivalent Circuit

Pin No.	Symbol	I/O	Equivalent circuit	Description
1	LD	O		APC amplifier output.
2	PD	I		APC amplifier input.
3	EQ_IN	I		Equalizer circuit input.
4	AC_SUM	O		RFAC summing amplifier output.
5	GND	—	—	Ground.

Pin No.	Symbol	I/O	Equivalent circuit	Description
6	A	I		RF summing amplifier and focus error amplifier input.
7	B	I		
8	C	I		
9	D	I		
10	E	I		Tracking error amplifier input.
11	F	I		
16	TE	O		Tracking error amplifier output.
12	SW	I		CD-ROM/RW switching input. RW when connected to Vcc, ROM when connected to GND.
13	RFAC	O		RFAC amplifier output.
14	FE	O		Focus error amplifier output.
15	FEI	I		Focus error amplifier gain adjustment. The gain is adjusted by the external resistance value connected between this pin and Pin 14.

Pin No.	Symbol	I/O	Equivalent circuit	Description
17	V _{CC}	—	—	Power supply.
18	RFG	I		Sets the RFAC low-frequency gain.
19	BST	I		Input for adjusting the equalizer circuit boost amount.
20	VFC	I		Input for adjusting the equalizer circuit boost frequency with the control voltage.
21	RFC	I		Input for adjusting the equalizer circuit boost frequency with external resistance.
22	VC	O		(V _{CC} + GND)/2 voltage output.
23	RFDC	O		RFDC amplifier output. This pin serves as the eye pattern check point.
24	RFDCI	I		RFDC amplifier gain adjustment. The gain is adjusted by the external resistance value connected between this pin and Pin 23.

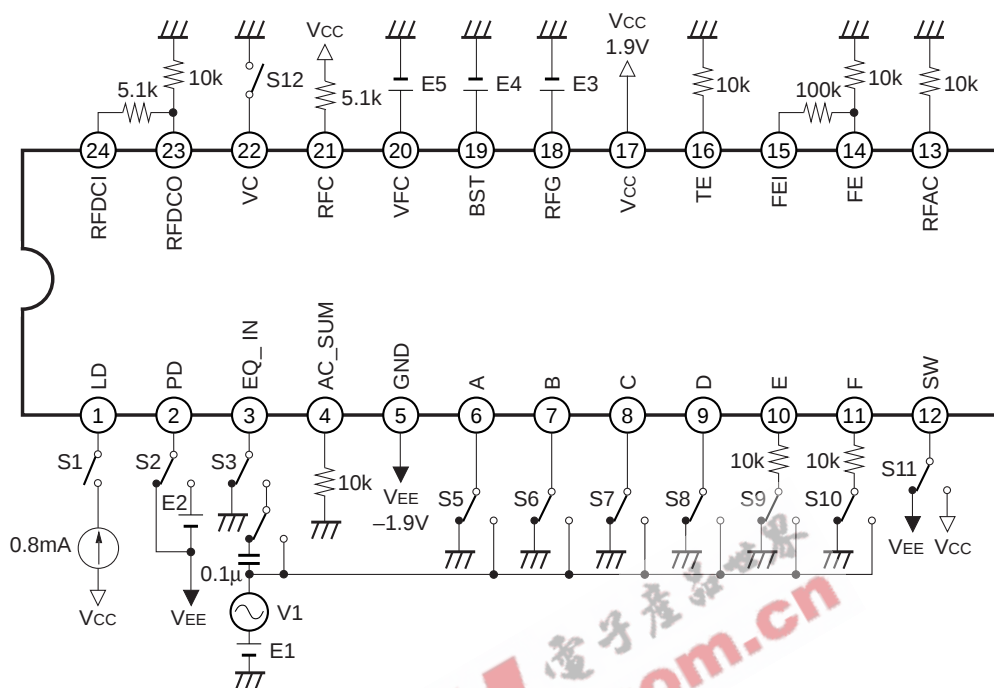
(V_{CC} = 1.9V, V_{EE} = -1.9V)

Electrical Characteristics

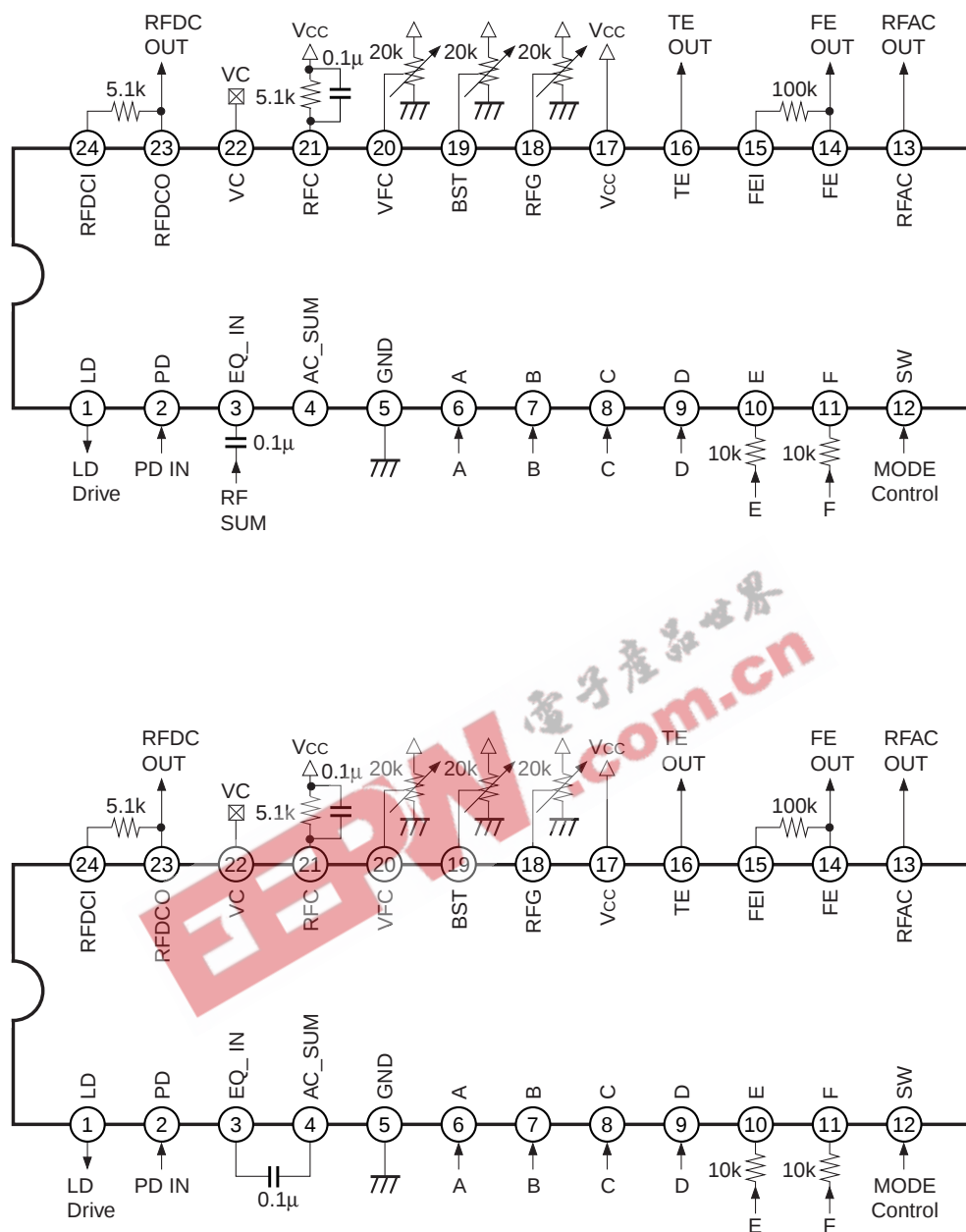
Measure- ment No.	Function	Measurement item	Symbol	Switch conditions												Bias conditions					Measure- ment pin	Measurement conditions	Min.	Typ.	Max.	Unit		
				S1	S2	S3	S4	S5	S6	S7	S8	S9	S10	S11	S12	V _i amplitude	V _i frequency	E1	E2	E3							E4	E5
1		Current consumption (Active, EQ On)	I _{cc_Aeqon}														0V	0V	0V	0V	0V	17	Pin current	25	45	65	mA	
2		Current consumption (Active, EQ Off)	I _{cc_Aeqoff}																	1.9V		17	Pin current	10	25	40	mA	
3		Current consumption (Sleep)	I _{cc_Slp}											Hi-Z						0V		17	Pin current	3.0	5	7.5	mA	
4		SUM offset voltage	ACSUM_Ofst																			4	Pin voltage	-1.2	-0.6	0	V	
5		SUM frequency gain	Gsum													0.1Vp-p	100kHz					4	20 log (Vout/Vin)	14.0	16.0	18.0	dB	
6		SUM frequency response	Fsum													0.1Vp-p	30MHz	▼				4	20 log (Vout/Vin) – Gsum	-3.0	-1.5	0.3	dB	
7		SUM maximum output voltage H	Vsum_H															0.3V				4	Pin voltage	0.9	1.25	—	V	
8		SUM maximum output voltage L	Vsum_L															-0.3V				4	Pin voltage	—	-0.5	-0.3	V	
9		Offset voltage ROM	AC_OfstROM														0V					13	Pin voltage	-0.3	0	0.3	V	
10		Offset voltage RW	AC_OfstRW																▼			13	Pin voltage	-0.3	0	0.3	V	
11		Low-frequency gain ROM_min	Gac_ROM1													1.6Vp-p	100kHz					13	20 log (Vout/Vin) – Gac_ROM2	-11.0	-8.0	-5.0	dB	
12		Low-frequency gain ROM_cnt	Gac_ROM2													0.8Vp-p	100kHz					13	20 log (Vout/Vin)	-1.0	2.0	5.0	dB	
13		Low-frequency gain ROM_max	Gac_ROM3													0.3Vp-p	100kHz					13	20 log (Vout/Vin) – Gac_ROM2	5.0	8.0	11.0	dB	
14		Low-frequency gain RW_min	Gac_RW1													0.4Vp-p	100kHz					13	20 log (Vout/Vin) – Gac_RW2	-11.0	-8.0	-5.0	dB	
15		Low-frequency gain RW_cnt	Gac_RW2													0.2Vp-p	100kHz					13	20 log (Vout/Vin) – Gac_ROM2	9.0	12.0	15.0	dB	
16		Low-frequency gain RW_max	Gac_RW3													75mVp-p	100kHz					13	20 log (Vout/Vin) – Gac_RW2	5.0	8.0	11.0	dB	
17		Low-frequency gain EQ_off	Gac_EQoff													0.8Vp-p	100kHz					13	20 log (Vout/Vin)	-1.0	2.0	5.0	dB	
18		Frequency response Min_L	Fac_MinL													0.2Vp-p	10MHz					13	20 log (Vout/Vin) – Gac_ROM2	3.5	6.0	8.5	dB	
19		Frequency response Min_H	Fac_MinH													0.2Vp-p	30MHz				▼	1.9V	13	20 log (Vout/Vin) – Gac_ROM2	3.5	6.0	8.5	dB
20		Frequency response EQ_OFF	Fac_ECoff													0.8Vp-p	30MHz	▼				1.9V	13	20 log (Vout/Vin) – Gac_EQoff	-2.0	-1.0	-0.5	dB
21		Maximum output voltage H	Vac_H															2V				0V	13	Pin voltage – AC_OfstROM	0.6	0.8	—	V
22		Maximum output voltage L	Vac_L															-2V					13	Pin voltage – AC_OfstROM	—	-0.8	-0.6	V
23		Offset voltage ROM	DC_OfstROM															0V				23	Pin voltage	-150	0	150	mV	
24		Offset voltage RW	DC_OfstRW																			23	Pin voltage	-100	0	400	mV	
25		Low-frequency gain ROM	Gdc_ROM													0.1Vp-p	100kHz					23	20 log (Vout/Vin)	16.5	19.5	22.5	dB	
26		Low-frequency gain RW	Gdc_RW													25mVp-p	100kHz					23	20 log (Vout/Vin)	29.0	32.0	35.0	dB	
27		Frequency response ROM	Fdc_ROM													0.1Vp-p	10MHz					23	20 log (Vout/Vin) – Gdc_ROM	-3.5	-1.5	-0.5	dB	
28		Frequency response RW	Fdc_RW													25mVp-p	10MHz	▼				23	20 log (Vout/Vin) – Gdc_RW	-6.0	-3.0	-0.5	dB	
29		Maximum output voltage H	Vdc_H															0.25V				23	Pin voltage	1.3	1.6	—	V	
30		Maximum output voltage L	Vdc_L															-0.25V				23	Pin voltage	—	-1.0	-0.6	V	

Function	Measurement item	Symbol	Switch conditions												Bias conditions					Measure- ment pin	Measurement conditions	Min.	Typ.	Max.	Unit		
			S1	S2	S3	S4	S5	S6	S7	S8	S9	S10	S11	S12	V _i amplitude	V _i frequency	E1	E2	E3							E4	E5
31	Offset voltage ROM	FE_OfsROM															0V	0V	0V	0V	0V	14	Pin voltage	-150	0	150	mV
32	Offset voltage RW	FE_OfsRW									○											14	Pin voltage	-150	0	150	mV
33	Low-frequency gain ROM1	Gfe_ROM1											0.1Vp-p	10kHz								14	20 log (Vout/Vin)	13.0	16.0	19.0	dB
34	Low-frequency gain ROM2	Gfe_ROM2									○		0.1Vp-p	10kHz								14	20 log (Vout/Vin)	13.0	16.0	19.0	dB
35	Low-frequency gain RW1	Gfe_RW1									○		25mVp-p	10kHz								14	20 log (Vout/Vin)	25.0	28.0	31.0	dB
36	Low-frequency gain RW2	Gfe_RW2									○		25mVp-p	10kHz								14	20 log (Vout/Vin)	25.0	28.0	31.0	dB
37	Frequency response ROM1	Ffe_ROM1									○		0.1Vp-p	100kHz								14	20 log (Vout/Vin) – Gfe_ROM1	-3.5	-0.5	0.3	dB
38	Frequency response ROM2	Ffe_ROM2									○		0.1Vp-p	100kHz								14	20 log (Vout/Vin) – Gfe_ROM2	-3.5	-0.5	0.3	dB
39	Frequency response RW1	Ffe_RW1									○		25mVp-p	50kHz								14	20 log (Vout/Vin) – Gfe_RW1	-3.5	-0.5	0.3	dB
40	Frequency response RW2	Ffe_RW2									○		25mVp-p	50kHz								14	20 log (Vout/Vin) – Gfe_RW2	-3.5	-0.5	0.3	dB
41	Maximum output voltage H	Vfe_H									○						0.3V					14	Pin voltage	1.2	1.7	—	V
42	Maximum output voltage L	Vfe_L									○						-0.3V					14	Pin voltage	—	-1.5	-1.1	V
43	Offset voltage ROM	TE_OfsROM															0V					16	Pin voltage	-150	0	150	mV
44	Offset voltage RW	TE_OfsRW									○											16	Pin voltage	-150	0	150	mV
45	Low-frequency gain ROM1	Gte_ROM1											0.1Vp-p	10kHz								16	20 log (Vout/Vin)	17.0	20.0	23.0	dB
46	Low-frequency gain ROM2	Gte_ROM2										○	0.1Vp-p	10kHz								16	20 log (Vout/Vin)	17.0	20.0	23.0	dB
47	Low-frequency gain RW1	Gte_RW1									○		25mVp-p	10kHz								16	20 log (Vout/Vin)	29.0	32.0	35.0	dB
48	Low-frequency gain RW2	Gte_RW2									○		25mVp-p	10kHz								16	20 log (Vout/Vin)	29.0	32.0	35.0	dB
49	Frequency response ROM1	Fte_ROM1											0.1Vp-p	200kHz								16	20 log (Vout/Vin) – Gte_ROM1	-1.5	0	1.5	dB
50	Frequency response ROM2	Fte_ROM2										○	0.1Vp-p	200kHz								16	20 log (Vout/Vin) – Gte_ROM2	-1.5	0	1.5	dB
51	Frequency response RW1	Fte_RW1									○		25mVp-p	200kHz								16	20 log (Vout/Vin) – Gte_RW1	-4.5	-2.0	-0.2	dB
52	Frequency response RW2	Fte_RW2										○	25mVp-p	200kHz								16	20 log (Vout/Vin) – Gte_RW2	-4.5	-2.0	-0.2	dB
53	Maximum output voltage H	Vte_H										○					0.3V					16	Pin voltage	1.2	1.7	—	V
54	Maximum output voltage L	Vte_L															-0.3V					16	Pin voltage	—	-1.5	-1.1	V
55	Output voltage 1	Vapc1		○													0V					1	Input where output voltage = 0V	85	135	185	mV
56	Output voltage 2	Vapc2																	-30mV			1	Pin voltage	0.45	0.7	0.95	V
57	Output voltage 3	Vapc3																	30mV			1	Pin voltage	-0.95	-0.7	-0.45	V
58	APC OFF voltage	Vapc_off																	0V			1	Pin voltage	1.4	1.6	—	V
59	Maximum output current	Iapc_max		○																		1	Pin voltage	-0.2	0	0.6	V
60	Output voltage	V _{CC}										○										22	Pin voltage	-100	0	100	mV

Electrical Characteristics Measurement Circuit



Application Circuits

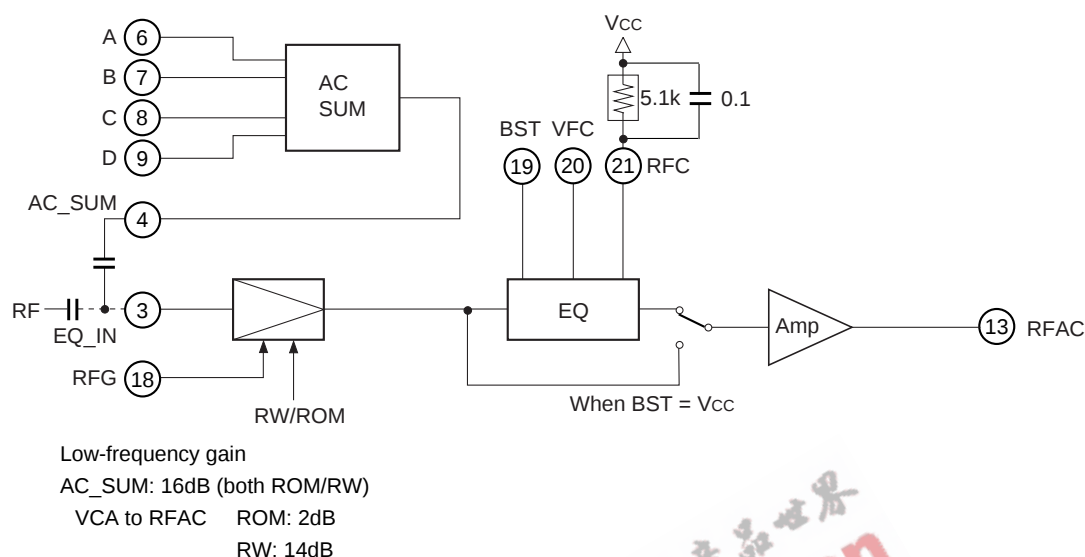


Application circuits shown are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits or for any infringement of third party patent and other right due to same.

Description of Functions

• RFAC

The RF signal input by connecting capacitance to the EQ_IN pin is equalized, arithmetically amplified and then output from the RFAC pin.



The EQ can be bypassed by connecting the BST control pin (Pin 19) to V_{CC} . In this case only the EQ block enters sleep mode and the low power consumption mode (slim mode) is activated. The low-frequency gain is the same value as for EQ ON mode.

The RF_SUM input dynamic range is $V_C \pm 300\text{mV}$ (typ.).

If RF (summing signal) is present at the pickup output pin, input the addition output signal to the EQ_IN pin (Pin 3) coupled by capacitance.

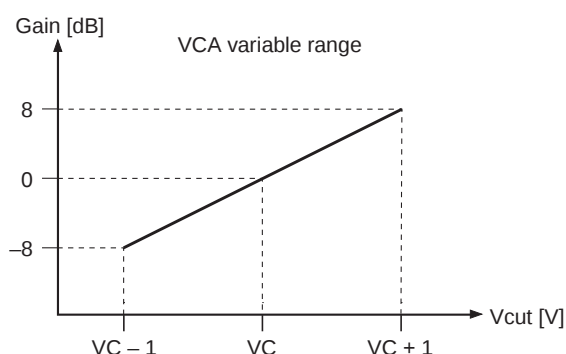
When using a pickup without a summing output function, perform addition with the AC SUM block and then input the signal to the EQ_IN pin coupled by capacitance.

RW/ROM switching is done by the VCA block, so either input method can be used without problem.

The RW gain is 12dB higher than the ROM gain.

The VCA low-frequency gain can be adjusted by the RFG pin (Pin 18) voltage.

The control voltage vs. low-frequency gain characteristics are shown in the graph to the right.



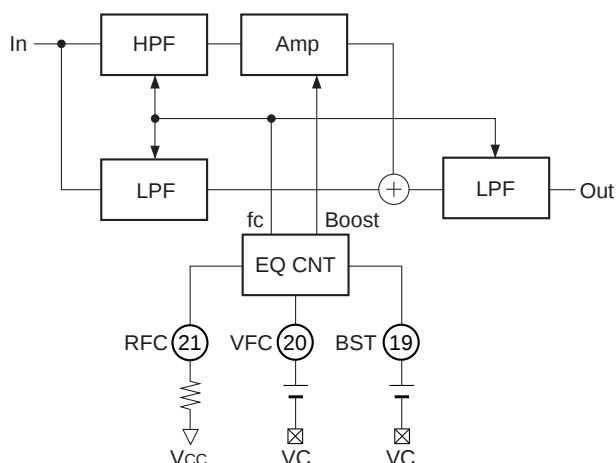
The RFAC pin (Pin 13) is an NPN transistor emitter follower output.

The maximum drive current is approximately 2mA.

If the load capacitance distorts the output waveform, increase the drive current.

Connect resistance between Pin 13 and GND.

• EQ



The diagram to the left shows the EQ internal block diagram.

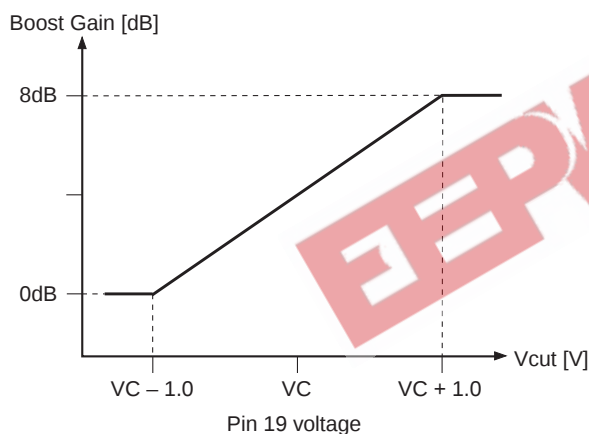
The EQ consists of a combination of HPF and LPF. The HPF and LPF transmittance is the Bessel function. The boost gain can be adjusted by adjusting the HPF gain.

The boost frequency is adjusted by the RFC external resistance value and the VFC control voltage value.

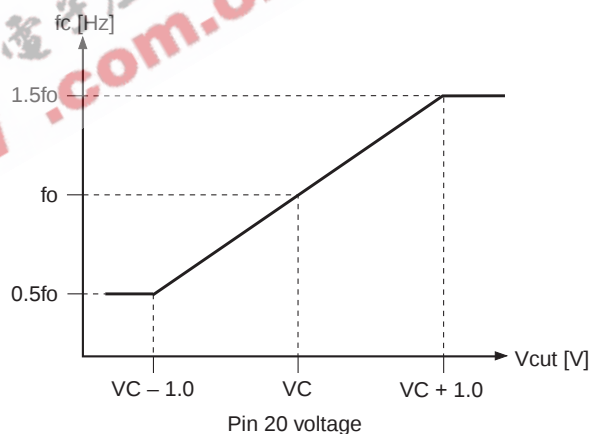
RFC resistance value: The cut-off frequency f_0 of each filter is adjusted by the Pin 21 external resistance value. The VFC voltage can be varied using this f_0 as the reference.

VFC voltage: f_0 can be changed by the voltage applied to Pin 20.

The boost gain can be adjusted by the BST pin control voltage. The control characteristics are shown in the graph below.

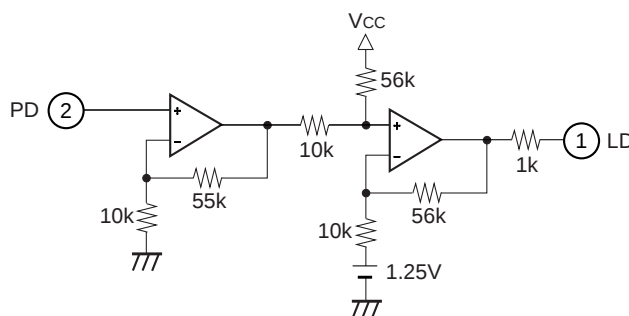


The cut-off frequency control characteristics are shown in the graph below.



• APC (Automatic Power Control)

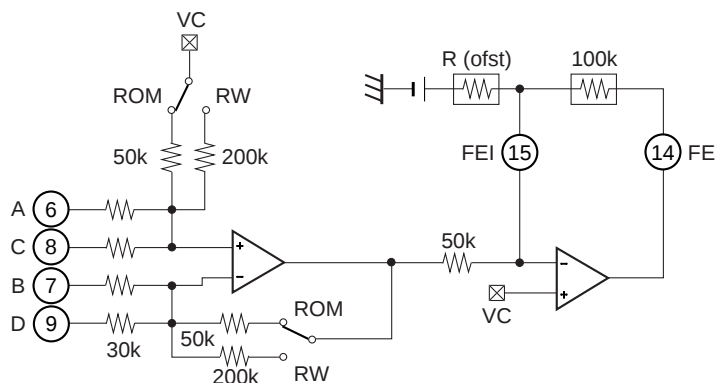
When the laser diode is driven by a constant current, the optical power output has extremely large negative temperature characteristics. Therefore, the current must be controlled to maintain the monitor photodiode output at a constant level. This control is performed by the APC function



• Focus Error

The signals input to the A and C pins and the B and D pins are arithmetically amplified and the focus error signal is output.

This circuit has RW/ROM switching, low-frequency gain adjustment and offset adjustment (external resistance) functions.



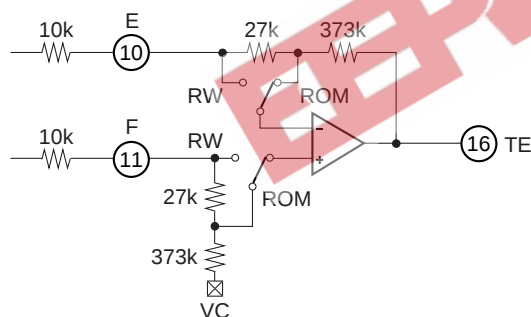
$$FE = \text{Gain} \{ (B + D) - (A + C) \}$$

Low-frequency gain	ROM: 16dB
	RW: 28dB
Cut-off frequency f_c (typ.)	ROM: 400kHz
	RW: 300kHz

• Tracking Error

The signals input to the E and F pins are arithmetically amplified and the tracking error signal is output.

This circuit has RW/ROM switching, low-frequency gain adjustment and offset adjustment (external resistance) functions.



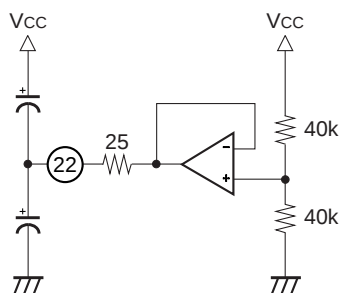
$$TE = \text{Gain} (F - E)$$

Low-frequency gain	ROM: 20dB
	RW: 32dB
f_c (typ.)	ROM: 1MHz
	RW: 250kHz

• VC Buffer

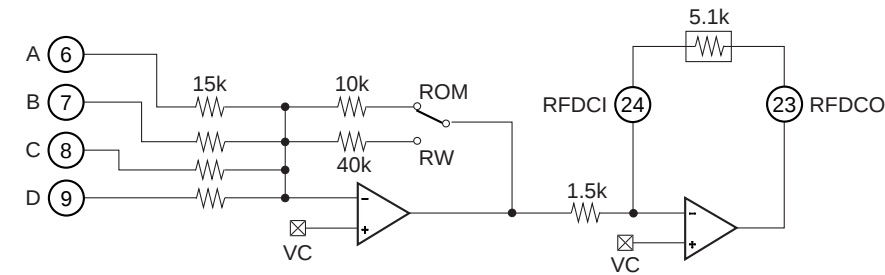
This outputs the VC ((1/2) V_{CC}) voltage.

The maximum output current is approximately $\pm 3\text{mA}$.



• RFDC

The signals input via the A, B, C and D pins are added, amplified and the RFDC signal is output. RW/ROM switching, low-frequency gain adjustment and offset adjustment are possible.



RFDC = Gain (A + B + C + D)
 Low-frequency gain ROM: 20dB
 RW: 32dB
 fc (Typ.) ROM: 12MHz
 RW: 5MHz
 The gain can be adjusted by the external resistance connected between Pins 23 and 24.

• SW

This controls the laser (APC) on/off, active/sleep mode, and RW/ROM mode switching. Switching is controlled by the voltage applied to the SW pin (Pin 12).



The VC buffer is kept active even in sleep mode.
 In the function block, BGR and MODE_SW are always set to active mode.

Item	APC	Active/Sleep	RW/ROM
Control voltage			
Vcc	ON	Active	RW
VC or Hi-Z	OFF	Sleep	—
GND	ON	Active	ROM

Notes on Operation

Stabilizing the RFAC signal

The RFAC system (RFSUM + EQ) is comprised entirely of non-inverted function blocks.

This is in order to support pickups with built-in RFSUM.

Therefore, if the voltage gain of each block is increased, a feedback loop is formed over the entire RFAC system causing the RFAC signal to become unstable (oscillate).

In these cases, it is recommended to lower the EQ frequency response and the boost gain. This has a large effect on the board (power supply, I/O signal cross talk, etc.) loop. The RFAC signal easily becomes unstable if the VCA gain is increased, the EQ boost frequency is set to a high frequency, the EQ boost amount is increased, etc.

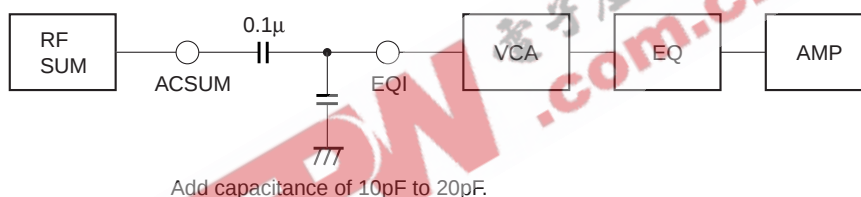
The VCA gain is low in ROM mode, so the RFAC signal is stable. Also, when not using RFSUM, the RFAC signal is stabilized because the overall gain is low.

The area where the RFAC signal becomes unstable is thought to vary for each set, as this is greatly affected by the board loop as noted above.

Proposed stabilization measures

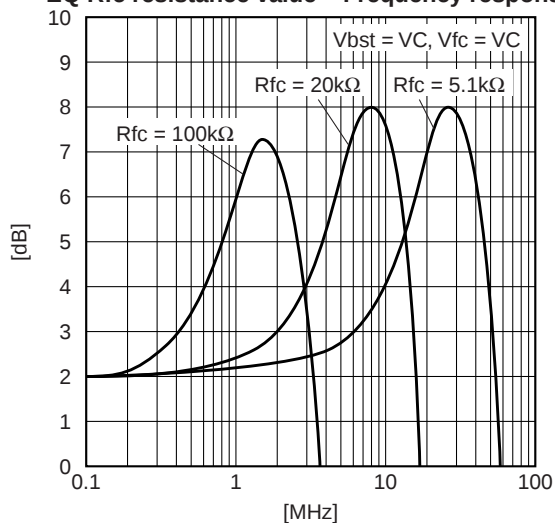
The board and other loop characteristics can be changed by adding external capacitance as noted below.

This has a particularly large effect on the stabilization when using RFSUM.

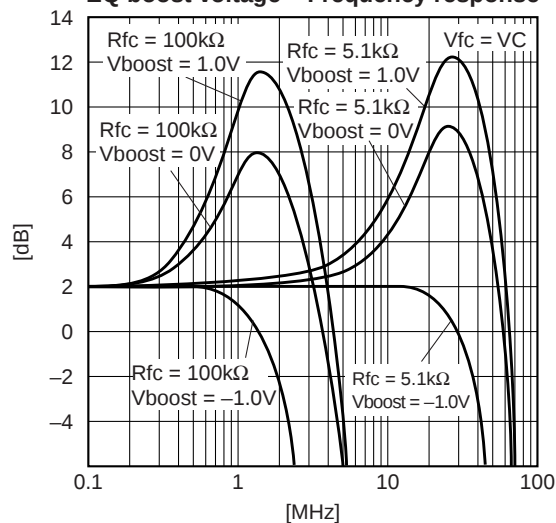


Example of Representative Characteristics

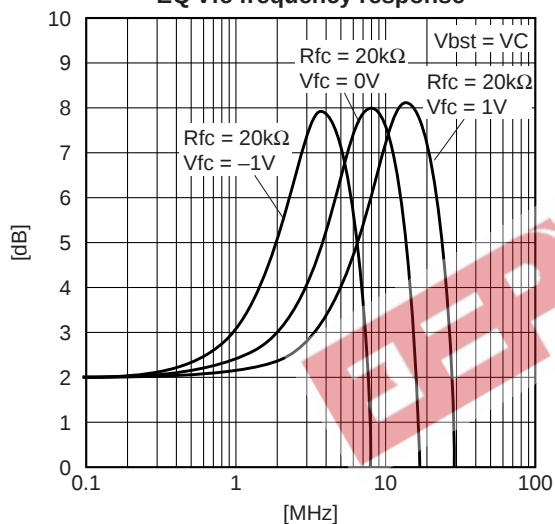
EQ Rfc resistance value – Frequency response



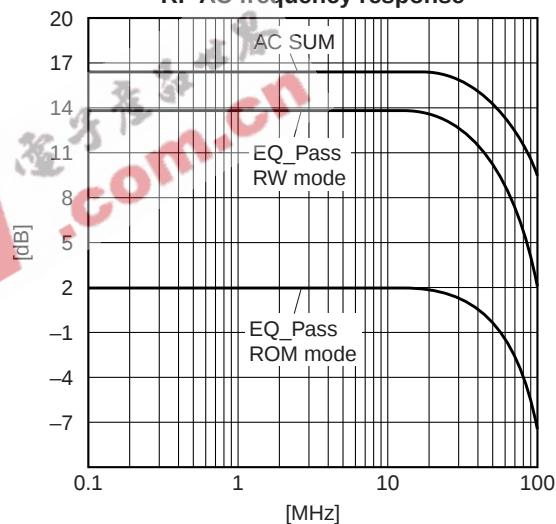
EQ boost voltage – Frequency response



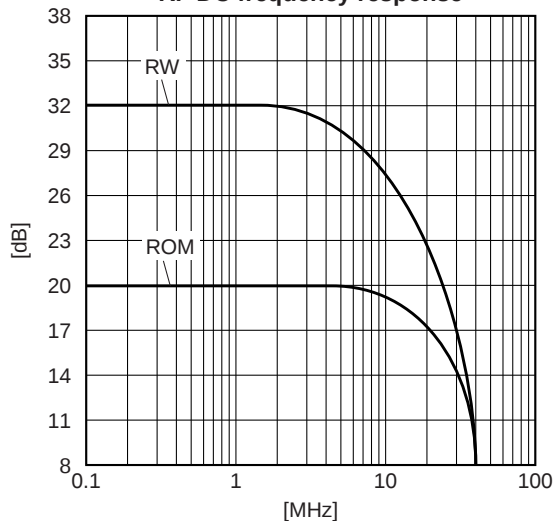
EQ Vfc frequency response



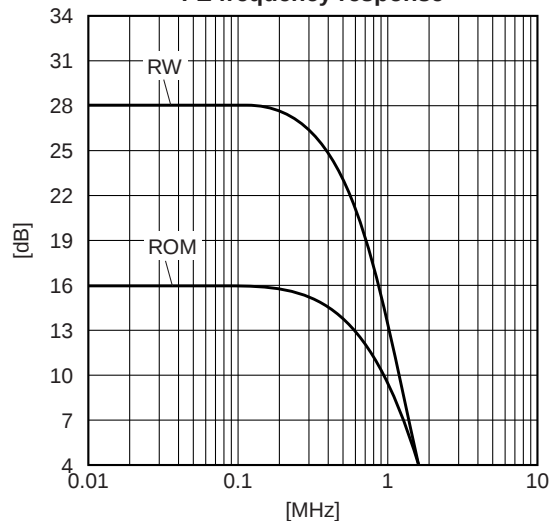
RF AC frequency response

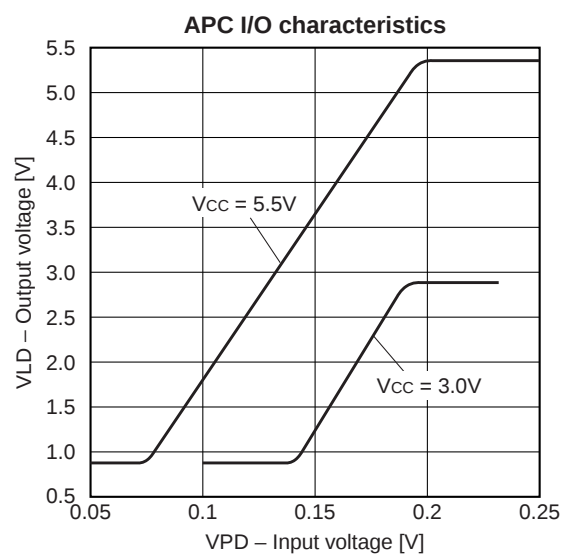
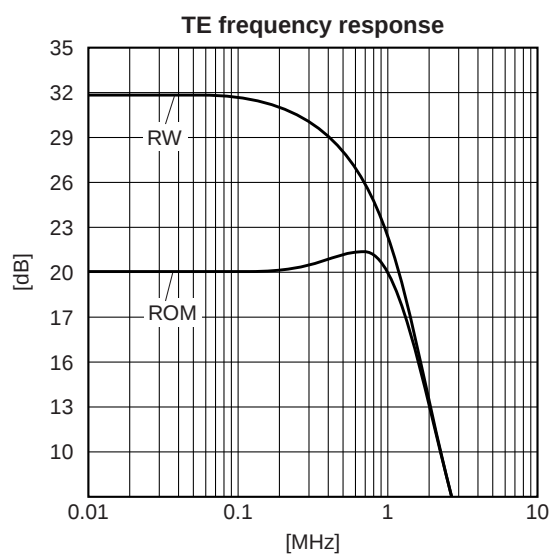


RF DC frequency response



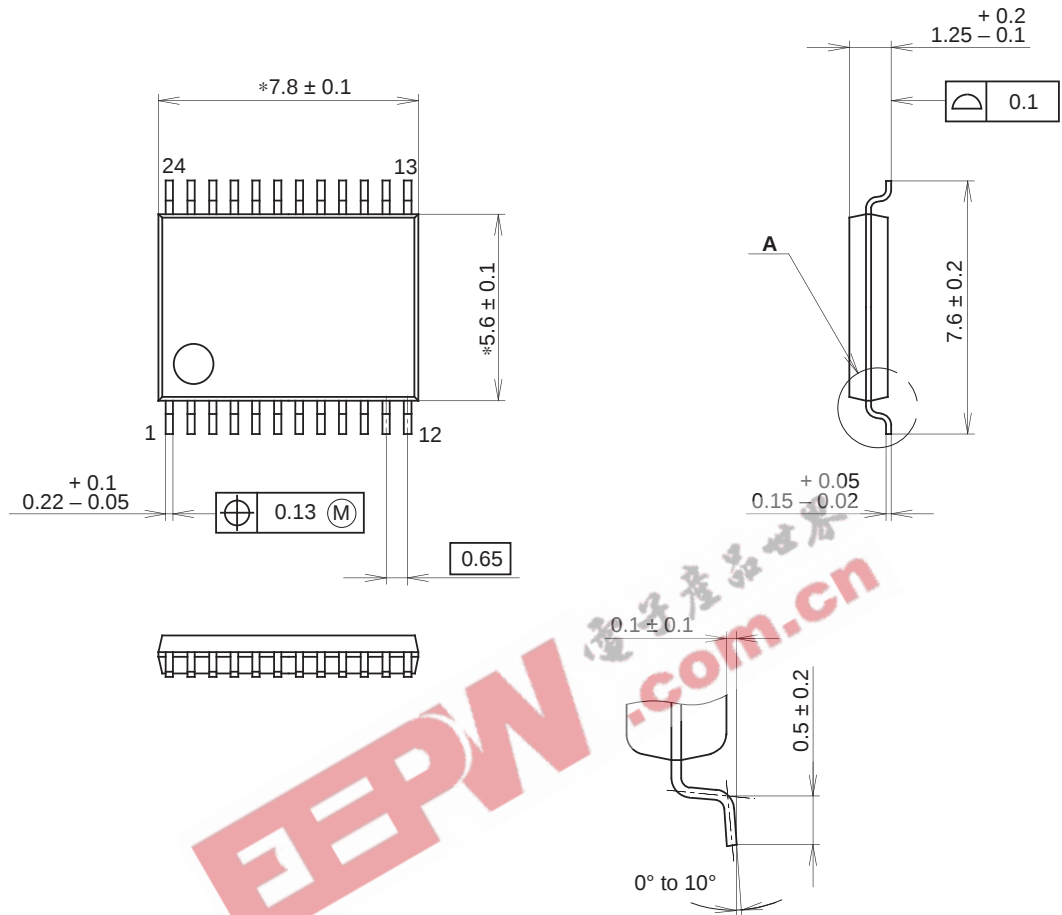
FE frequency response





Package Outline Unit: mm

24PIN SSOP(PLASTIC)



NOTE: Dimensions "*" does not include mold protrusion.

DETAIL A

PACKAGE STRUCTURE

SONY CODE	SSOP-24P-L01	PACKAGE MATERIAL	EPOXY RESIN
EIAJ CODE	SSOP024-P-0056	LEAD TREATMENT	SOLDER/PALLADIUM PLATING
JEDEC CODE		LEAD MATERIAL	42/COPPER ALLOY
		PACKAGE MASS	0.1g

NOTE : PALLADIUM PLATING
This product uses S-PdPPF (Sony Spec.-Palladium Pre-Plated Lead Frame).